

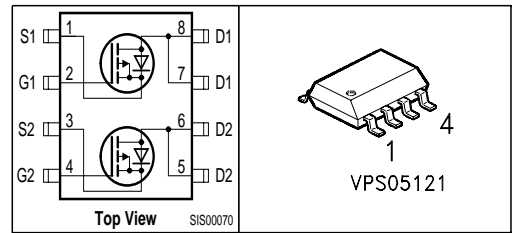
## OptiMOS<sup>®</sup>-P Small-Signal-Transistor

### Feature

- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- dv/dt rated

### Product Summary

|              |      |    |
|--------------|------|----|
| $V_{DS}$     | -20  | V  |
| $R_{DS(on)}$ | 21   | mΩ |
| $I_D$        | -8.2 | A  |



| Type    | Package | Ordering Code |
|---------|---------|---------------|
| BSO203P | SO 8    | Q67042-S4072  |

### Maximum Ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter  | Symbol              | Value        | Unit              |
|--|---------------------|--------------|-------------------|
| Continuous drain current<br>$T_A=25\text{ °C}$<br>$T_A=70\text{ °C}$   | $I_D$               | -8.2<br>-6.6 | A                 |
| Pulsed drain current<br>$T_A=25\text{ °C}$   | $I_{D\text{ puls}}$ | -32.8        |                   |
| Avalanche energy, single pulse<br>$I_D=-8.2\text{ A}$ , $V_{DD}=-10\text{ V}$ , $R_{GS}=25\text{ }\Omega$                        | $E_{AS}$            | 97           | mJ                |
| Reverse diode dv/dt<br>$I_S=-8.2\text{ A}$ , $V_{DS}=-16\text{ V}$ , $di/dt=200\text{ A}/\mu\text{s}$ , $T_{jmax}=150\text{ °C}$ | dv/dt               | -6           | kV/ $\mu\text{s}$ |
| Gate source voltage  | $V_{GS}$            | $\pm 12$     | V                 |
| Power dissipation<br>$T_A=25\text{ °C}$  | $P_{tot}$           | 2            | W                 |
| Operating and storage temperature  | $T_j, T_{stg}$      | -55... +150  | °C                |
| IEC climatic category; DIN IEC 68-1  |                     | 55/150/56    |                   |

**Thermal Characteristics**

| Parameter   | Symbol     | Values |      |      | Unit |
|---|------------|--------|------|------|------|
|   |            | min.   | typ. | max. |      |
| <b>Characteristics</b>  |            |        |      |      |      |
| Thermal resistance, junction - soldering point                                | $R_{thJS}$ | -      | -    | 50   | K/W  |
| SMD version, device on PCB:   | $R_{thJA}$ | -      | -    | 110  |      |
| @ min. footprint, $t < 10s$<br>@ 6 cm <sup>2</sup> cooling area <sup>1)</sup> |            | -      | -    | 62.5 |      |

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter  | Symbol        | Values |             |            | Unit      |
|--|---------------|--------|-------------|------------|-----------|
|  |               | min.   | typ.        | max.       |           |
| <b>Static Characteristics</b>  |               |        |             |            |           |
| Drain-source breakdown voltage<br>$V_{GS}=0, I_D=-250\mu A$  | $V_{(BR)DSS}$ | -20    | -           | -          | V         |
| Gate threshold voltage, $V_{GS} = V_{DS}$<br>$I_D=-100\mu A$   | $V_{GS(th)}$  | -0.6   | 0.9         | -1.2       |           |
| Zero gate voltage drain current<br>$V_{DS}=-20V, V_{GS}=0, T_j=25^\circ C$<br>$V_{DS}=-20V, V_{GS}=0, T_j=150^\circ C$ | $I_{DSS}$     | -      | -0.1<br>-10 | -1<br>-100 | $\mu A$   |
| Gate-source leakage current<br>$V_{GS}=-12V, V_{DS}=0$   | $I_{GSS}$     | -      | -10         | -100       |           |
| Drain-source on-state resistance<br>$V_{GS}=-2.5V, I_D=-6.4A$  | $R_{DS(on)}$  | -      | 26          | 35         | $m\Omega$ |
| Drain-source on-state resistance<br>$V_{GS}=-4.5, I_D=-8.2A$   | $R_{DS(on)}$  | -      | 18.6        | 21         |           |

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical without blown air;  $t \leq 10$  sec.

Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic Characteristics**

|                              |              |   |    |      |      |    |
|------------------------------|--------------|---|----|------|------|----|
| Transconductance             | $g_{fs}$     | $ V_{DS}  \geq 2 *  I_D  * R_{DS(on)max}$<br>$I_D = -6.6\text{A}$                   | 17 | 34   | -    | S  |
| Input capacitance            | $C_{iss}$    | $V_{GS} = 0, V_{DS} = -15\text{V},$<br>$f = 1\text{MHz}$                            | -  | 2242 | -    | pF |
| Output capacitance           | $C_{oss}$    |   | -  | 852  | -    |    |
| Reverse transfer capacitance | $C_{rss}$    |   | -  | 690  | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V},$<br>$I_D = -1\text{A}, R_G = 6\Omega$ | -  | 15.5 | 23.2 | ns |
| Rise time                    | $t_r$        |   | -  | 25.9 | 38.9 |    |
| Turn-off delay time          | $t_{d(off)}$ |   | -  | 59   | 88.5 |    |
| Fall time                    | $t_f$        |   | -  | 63.3 | 95   |    |

**Gate Charge Characteristics**

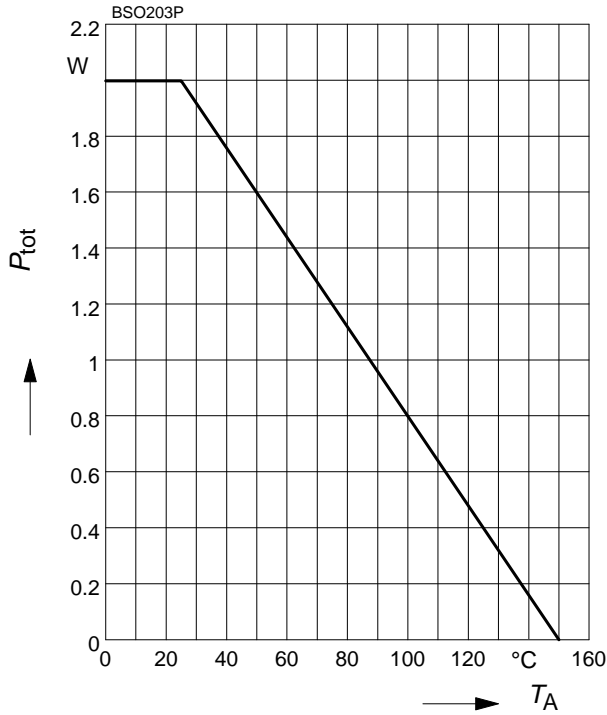
|                       |                 |  |   |       |       |    |
|-----------------------|-----------------|--|---|-------|-------|----|
| Gate to source charge | $Q_{gs}$        | $V_{DD} = -15\text{V}, I_D = -8.2\text{A}$   | - | -3.5  | -5.2  | nC |
| Gate to drain charge  | $Q_{gd}$        |  | - | -15.1 | -22.6 |    |
| Gate charge total     | $Q_g$           | $V_{DD} = -15\text{V}, I_D = -8.2\text{A},$<br>$V_{GS} = 0 \text{ to } -4.5\text{V}$ | - | -32.4 | -48.6 |    |
| Gate plateau voltage  | $V_{(plateau)}$ | $V_{DD} = -15\text{V}, I_D = -8.2\text{A}$   | - | -1.6  | -     | V  |

**Reverse Diode**

|  |          |  |   |      |       |    |
|--|----------|--|---|------|-------|----|
| Inverse diode continuous forward current | $I_S$    | $T_A = 25\text{ }^\circ\text{C}$   | - | -    | -2.5  | A  |
| Inverse diode direct current, pulsed     | $I_{SM}$ |  | - | -    | -32.8 |    |
| Inverse diode forward voltage            | $V_{SD}$ | $V_{GS} = 0, I_F = 8.2\text{A}$  | - | 0.85 | 1.3   | V  |
| Reverse recovery time                    | $t_{rr}$ | $V_R = -10\text{V},  I_F  =  I_D ,$<br>$di_F/dt = 100\text{A}/\mu\text{s}$ | - | 35.7 | 44.6  | ns |
| Reverse recovery charge                  | $Q_{rr}$ |  | - | 18.7 | 23.4  | nC |

### 1 Power dissipation

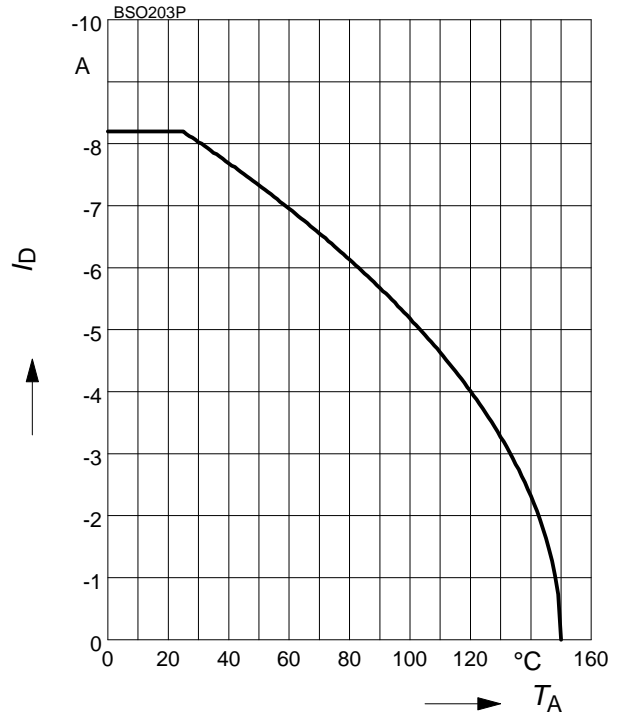
$$P_{tot} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

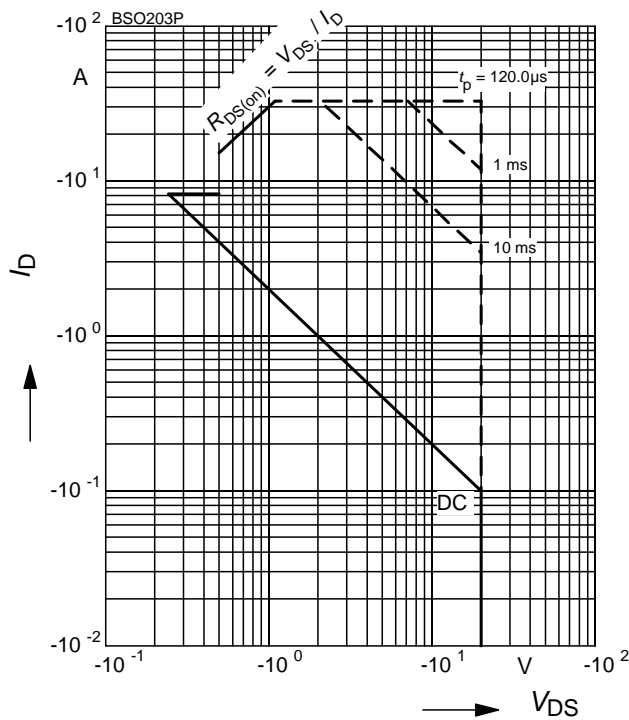
parameter:  $|V_{GS}| \geq 4.5 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

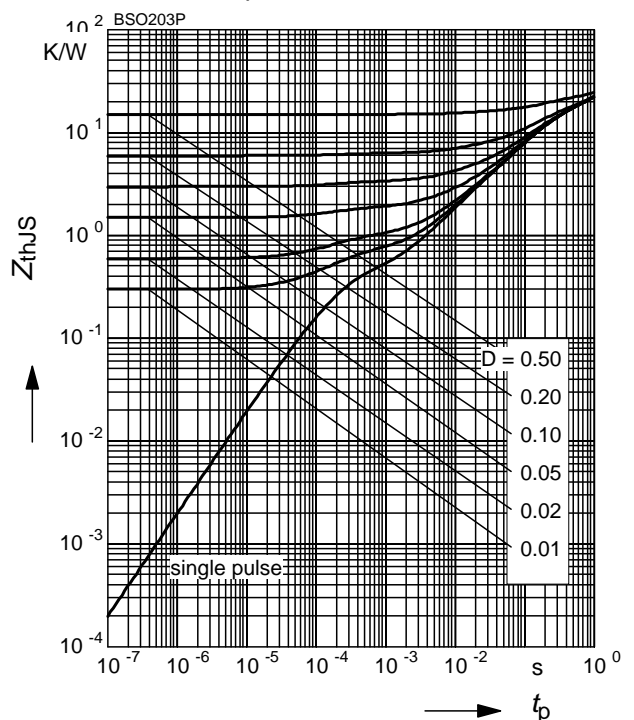
parameter:  $D = 0, T_A = 25 \text{ °C}$



### 4 Transient thermal impedance

$$Z_{thJS} = f(t_p)$$

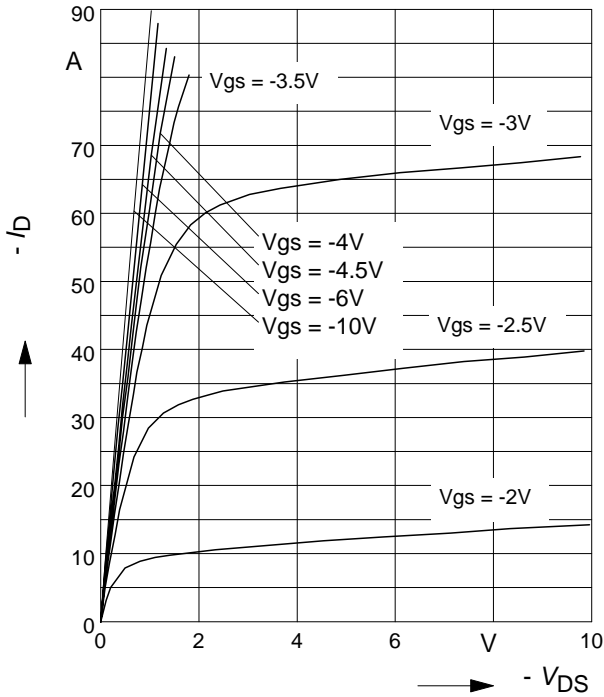
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

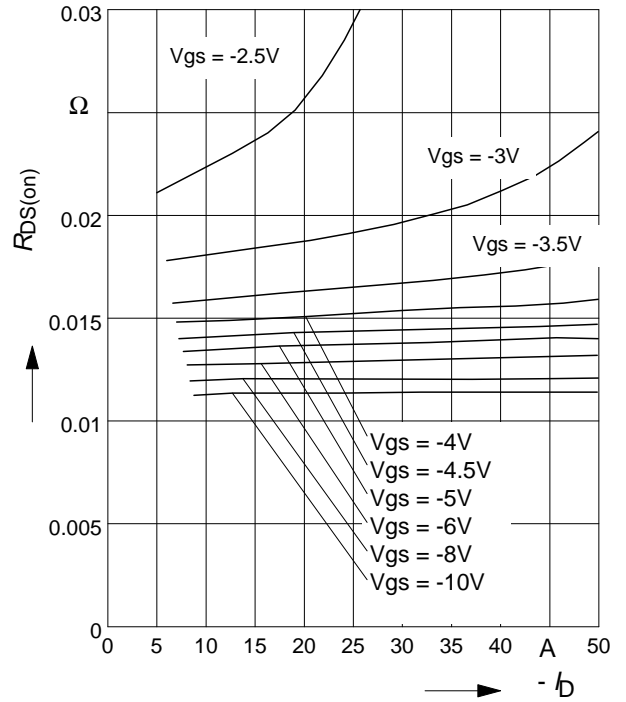
parameter:  $t_p = 80 \mu\text{s}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

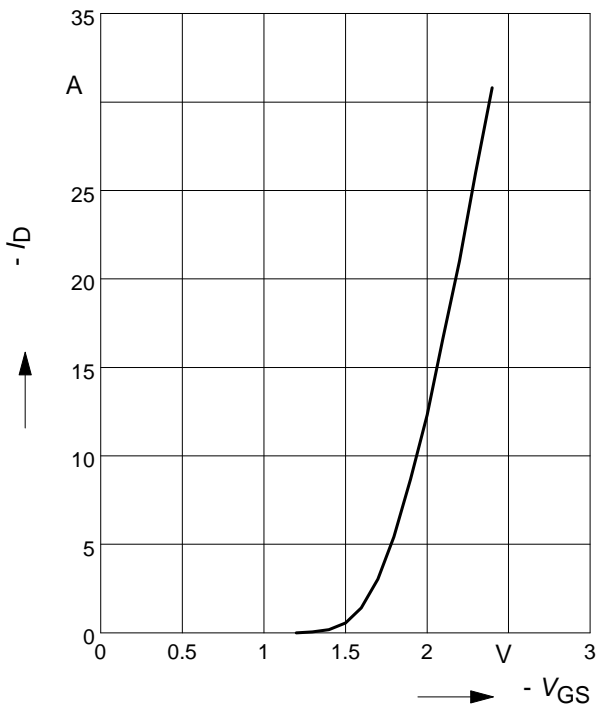
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

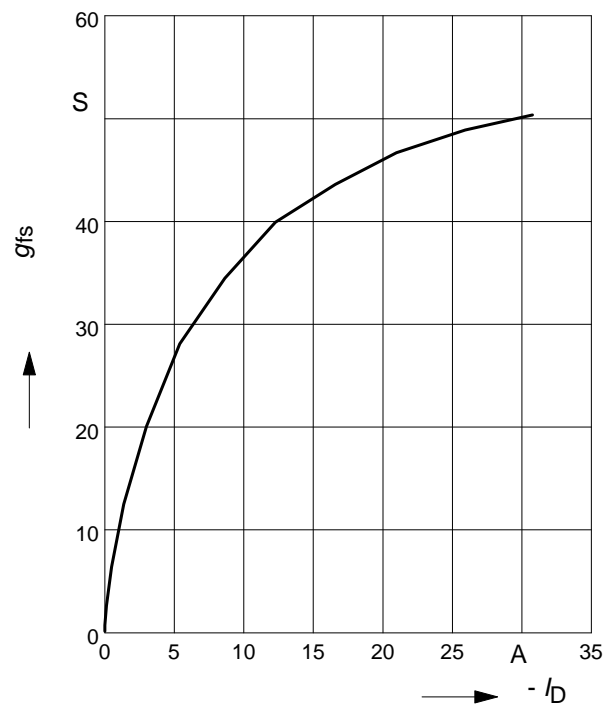
parameter:  $t_p = 80 \mu\text{s}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

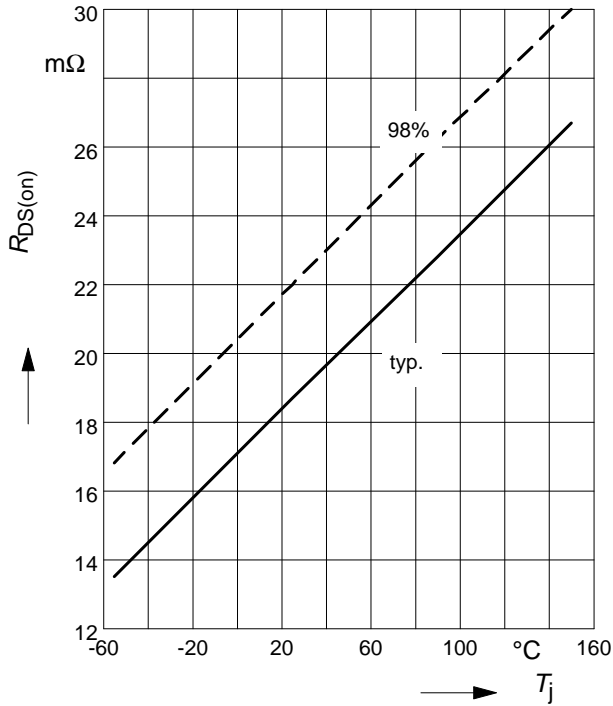
parameter:  $t_p = 80 \mu\text{s}$



**9 Drain-source on-resistance**

$$R_{DS(on)} = f(T_j)$$

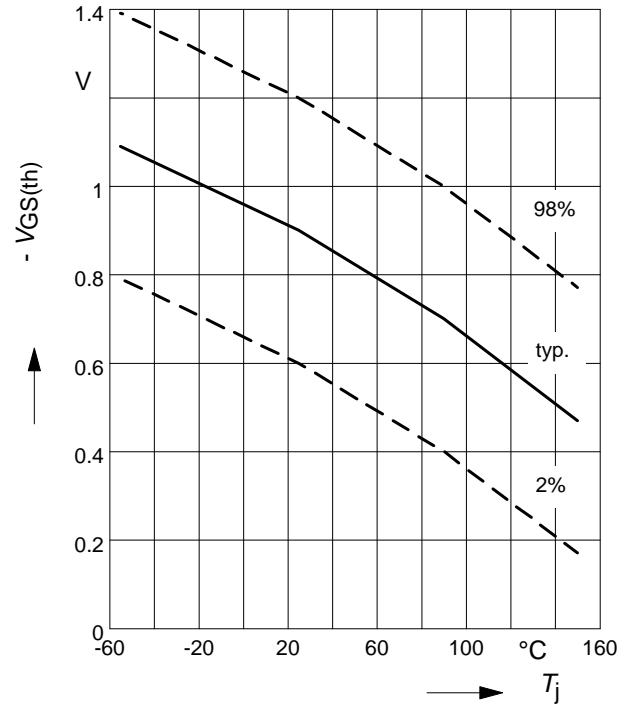
parameter:  $I_D = -8.2 \text{ A}$ ,  $V_{GS} = -4.5 \text{ V}$



**10 Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

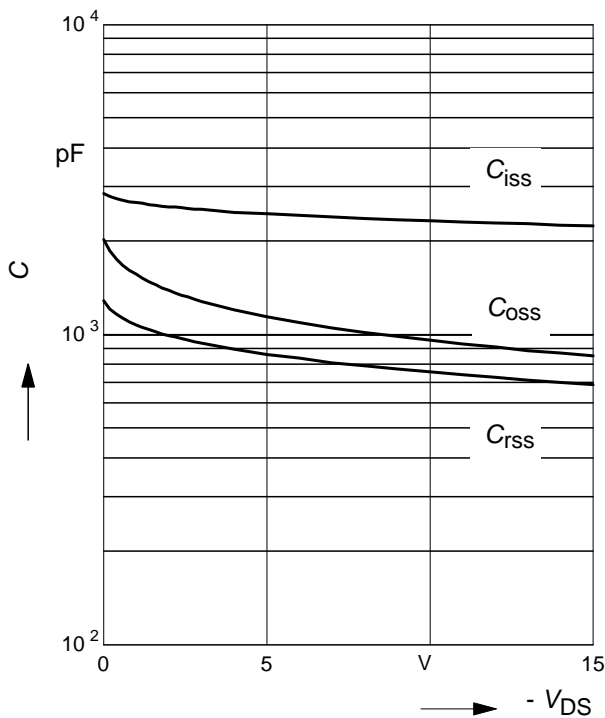
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = -100 \mu\text{A}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

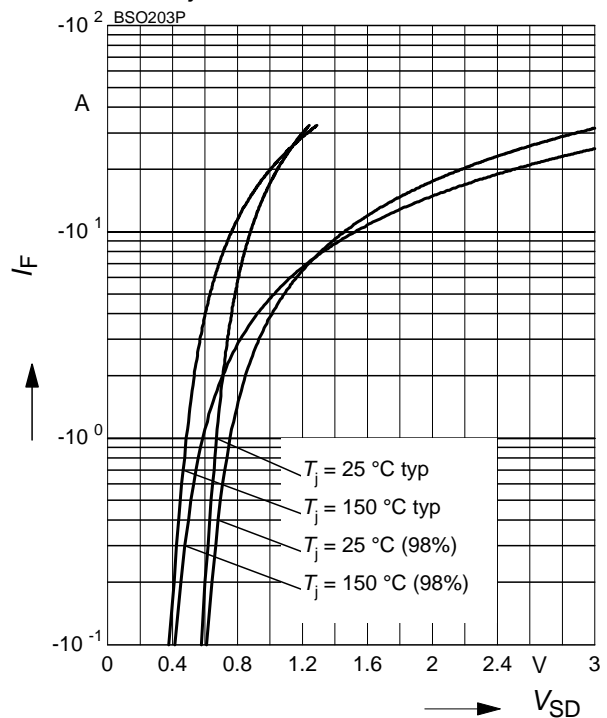
parameter:  $V_{GS} = 0$ ,  $f = 1 \text{ MHz}$



**12 Forward character. of reverse diode**

$$I_F = f(V_{SD})$$

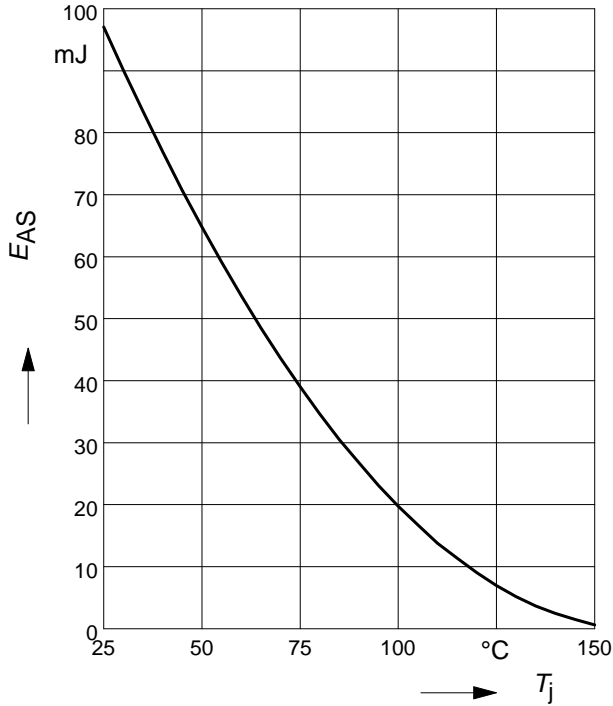
parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**13 Typ. avalanche energy**

$E_{AS} = f(T_j)$ , par.:  $I_D = -8.2\text{ A}$

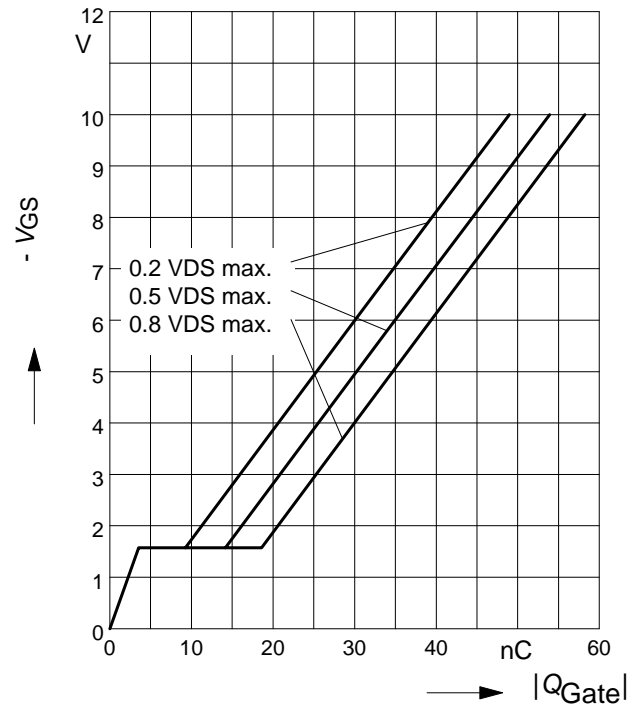
$V_{DD} = -10\text{ V}$ ,  $R_{GS} = 25\ \Omega$



**14 Typ. gate charge**

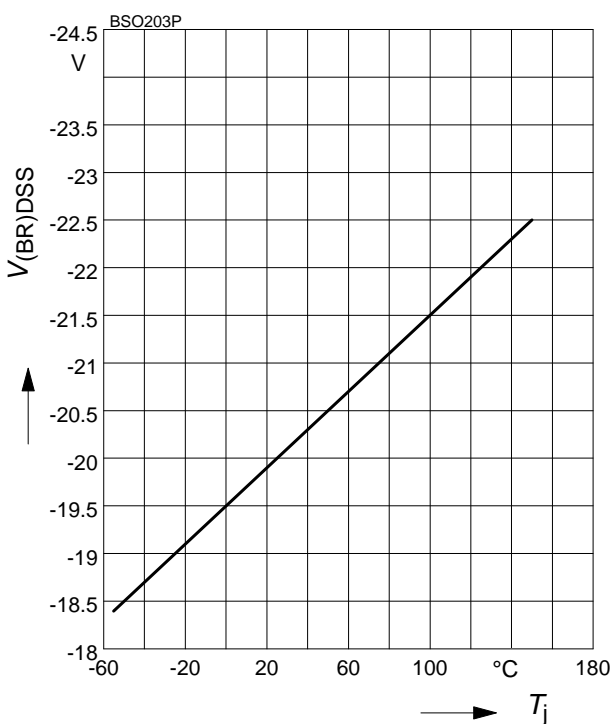
$|V_{GS}| = f(Q_{Gate})$

parameter:  $I_D = -8.2\text{ A}$  pulsed



**15 Drain-source breakdown voltage**

$V_{(BR)DSS} = f(T_j)$



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